

Supporting Information

N,S Co-doped 3D Mesoporous Carbon-Co₃Si₂O₅(OH)₄ Architectures for High-Performance Flexible Pseudo-Solid-State Supercapacitor

Xinran Li^a, Shiyuan Ding^a, Xiao Xiao^a, Jinying Shao^a, Jilei Wei^a, Huan Pang^{a*} and
Yan Yu^{b*}

- a. College of Chemistry and Chemical Engineering, Yangzhou University Yangzhou,
Jiangsu, 225002, Jiangsu, P. R. China, E-mail: huanpangchem@hotmail.com;
panghuan@yzu.edu.cn.
- b. CAS Key Laboratory of Materials for Energy Conversion, Department of
Materials Science and Engineering, University of Science and Technology of
China, Hefei 230026, Hefei, P. R. China. E-mail: yanyumse@ustc.edu.cn

Calculations

The mass-specific capacitance ($C/F\ g^{-1}$) of the device can also be calculated using :

$$C=Q / (m \times \Delta V) = \int Idt / (m \times \Delta V) = I \times t_{discharge} / (m \times \Delta V) \quad (1)$$

Where m is the mass of the activated materials, I is the discharge current, $t_{discharge}$ is discharge time, and ΔV is the potential drop during discharge.

The area-specific capacitance ($C/mF\ cm^{-2}$) of the device can also be calculated using :

$$C=Q / (A \times \Delta V) = \int Idt / (A \times \Delta V) = I \times t_{discharge} / (A \times \Delta V) \quad (2)$$

Where A is the surface area of the device, I is the discharge current, $t_{discharge}$ is discharge time, and ΔV is the potential drop during discharge.

The energy density and power density of the device can be obtained from :

$$E=0.5C \times V^2 \quad (3)$$

$$P=E/t_{discharge} \quad (4)$$

Where V represents the operating voltage.

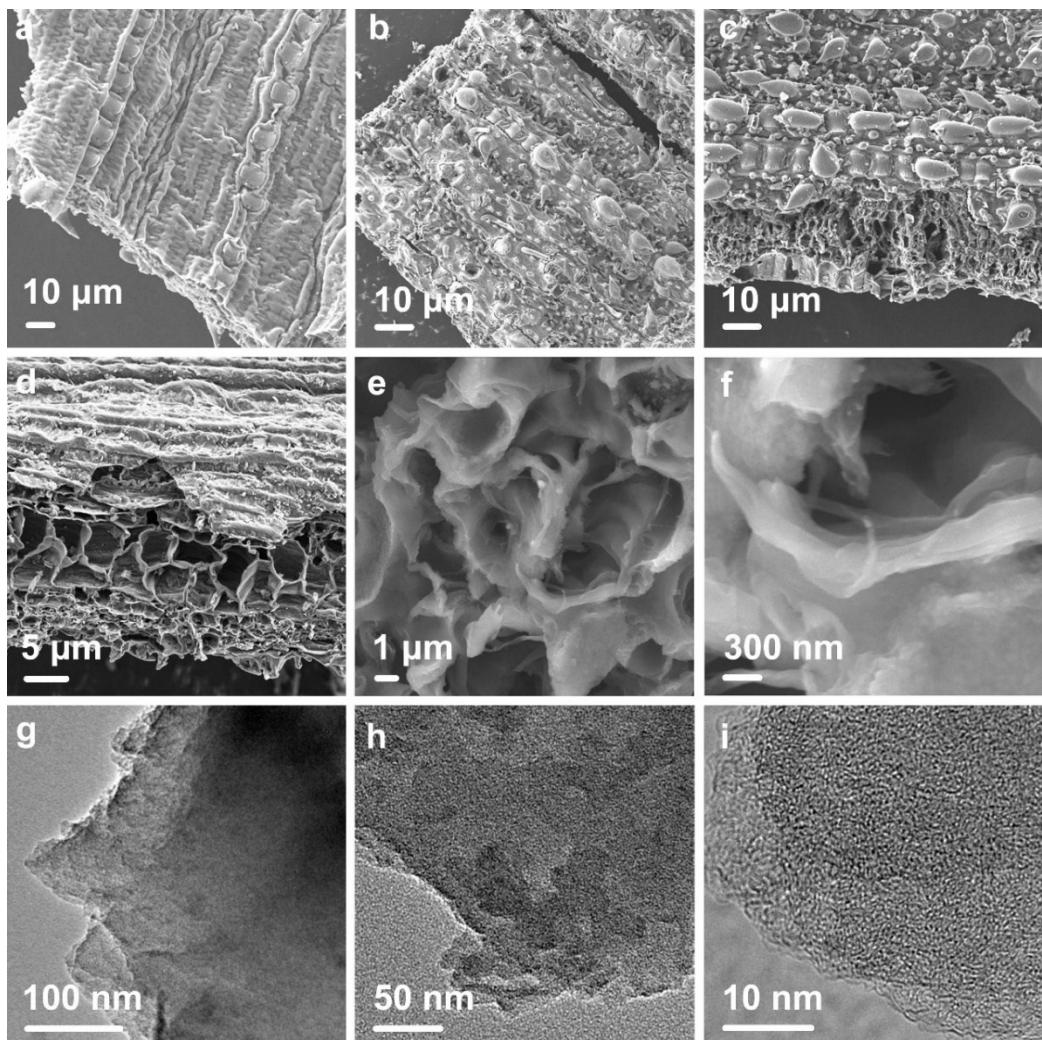


Figure S1. a-f) SEM images of as-prepared samples (N,S co-doped 3D mesoporous C-SiO₂ architectures), and g-i) Corresponding TEM images.

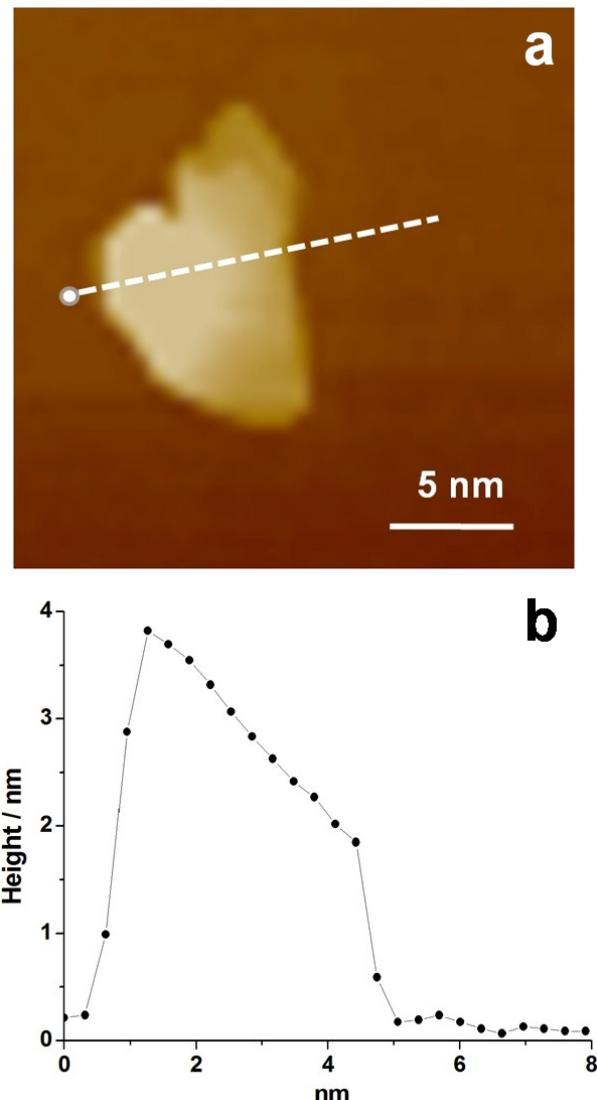


Figure S2. Atomic force microscope (AFM) image of $\text{Co}_3\text{Si}_2\text{O}_5(\text{OH})_4$ ultrathin nanoflakes.

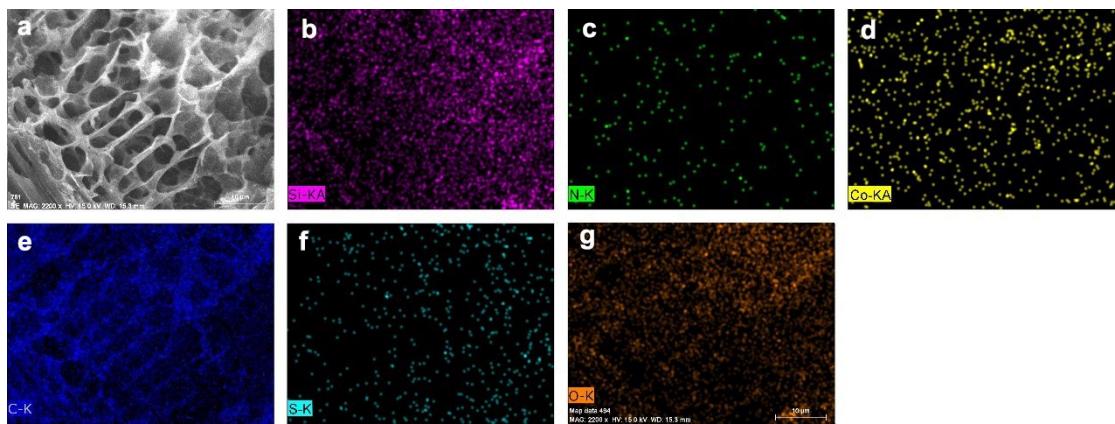


Figure S3. The corresponding EDS mappings of N,S co-doped 3D mesoporous C- $\text{Co}_3\text{Si}_2\text{O}_5(\text{OH})_4$ architectures: a) SEM image, b) Purple-Si-K, c) Green-N-K, d) Yellow-Co-K, e) Blue-C-K, f) Cyan-S-K, and g) Orange-O-K, respectively.

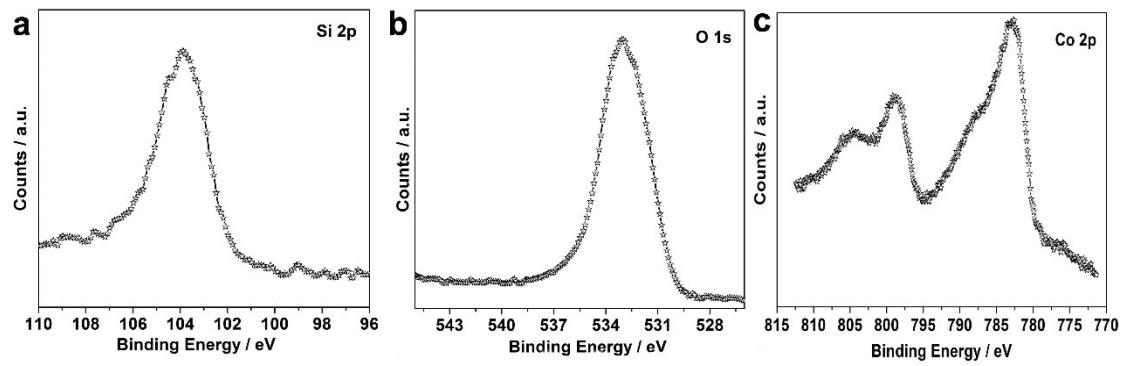


Figure S4. The high-resolution spectra of the N,S co-doped 3D mesoporous C-
Co₃Si₂O₅(OH)₄ architectures (a) Si 2p, (b) O 1s, and (c) Co 2p.

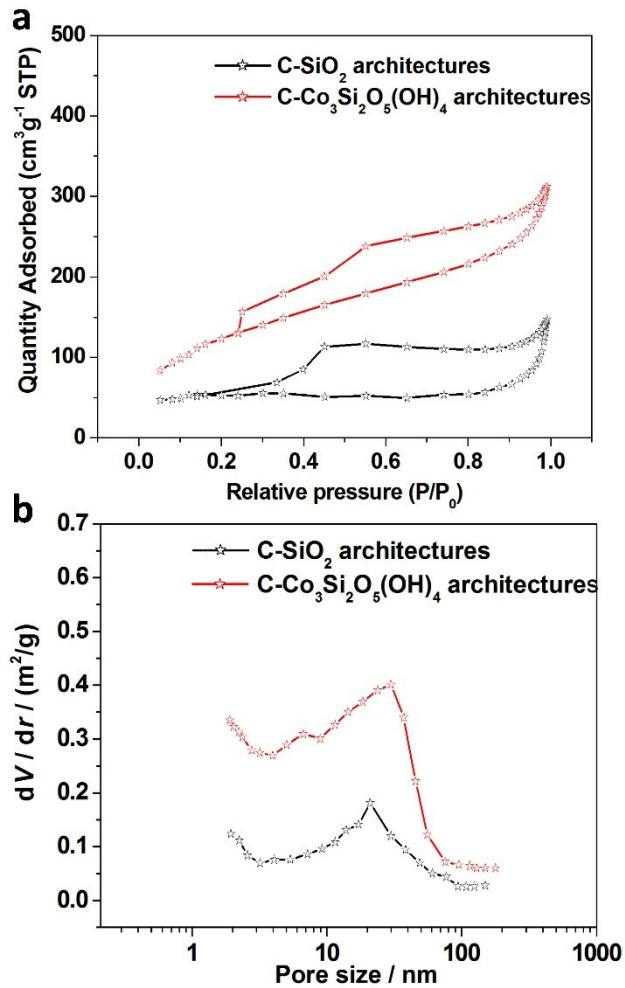


Figure S5. a) N₂ adsorption-desorption isotherm, and (b) the corresponding pore size distribution curve of as-prepared samples (3D mesoporous C-SiO₂ architectures, and N,S co-doped 3D mesoporous C-Co₃Si₂O₅(OH)₄ architectures).

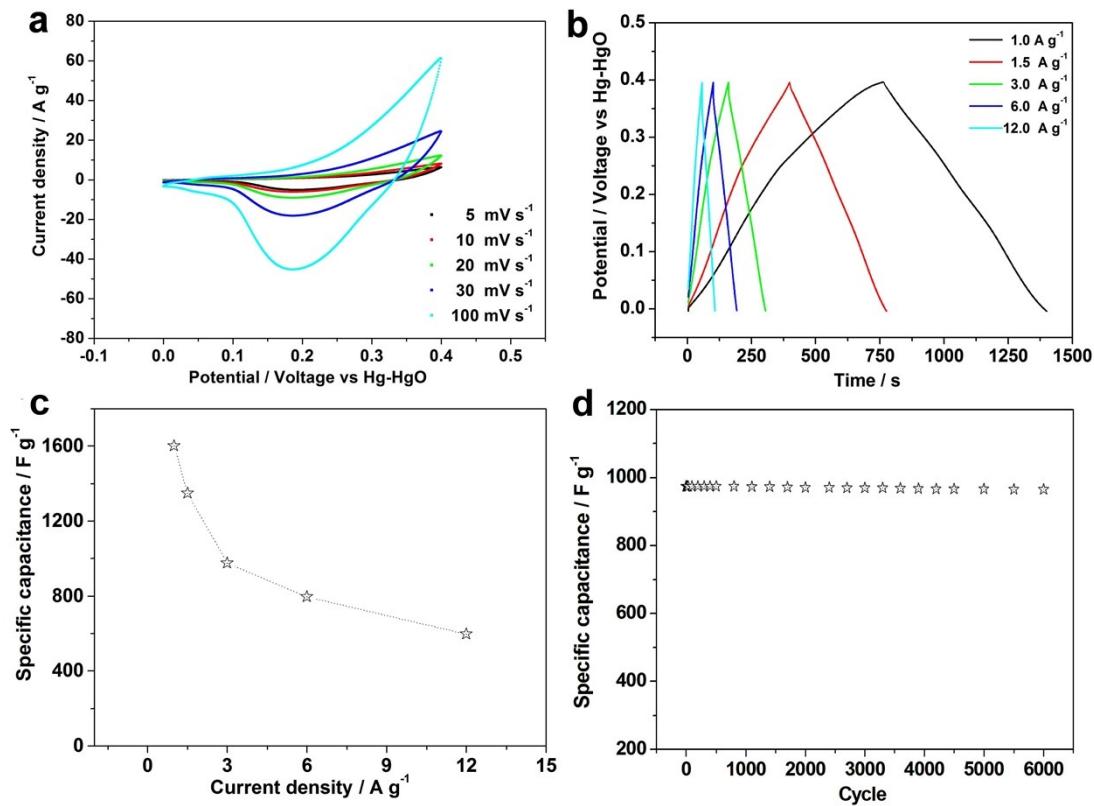


Figure S6. a) Cyclic voltammetry within 0 to 0.4 V range at different scan rates of 5-100 mV s^{-1} was performed on the as-prepared electrodes in 3.0 M KOH at room temperature, b) The galvanostatic discharge curves at 1.0-12.0 A g^{-1} , c) Specific capacitance obtained from different current densities, and d) Cycling performance of the device at 3.0 A g^{-1} for 6000 cycles.

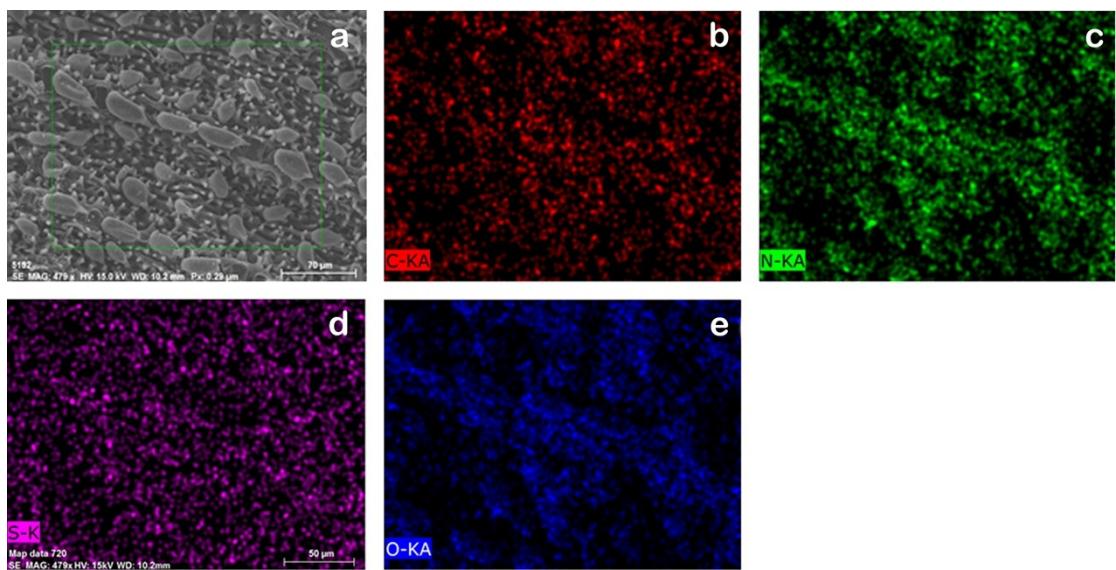


Figure S7. The corresponding EDS mappings of N,S co-doped pure carbon architectures (600 °C): a) SEM image, b) Red-C-K, c) Green-N-K, d) Purple-S-K, e) Blue-O-K, respectively.

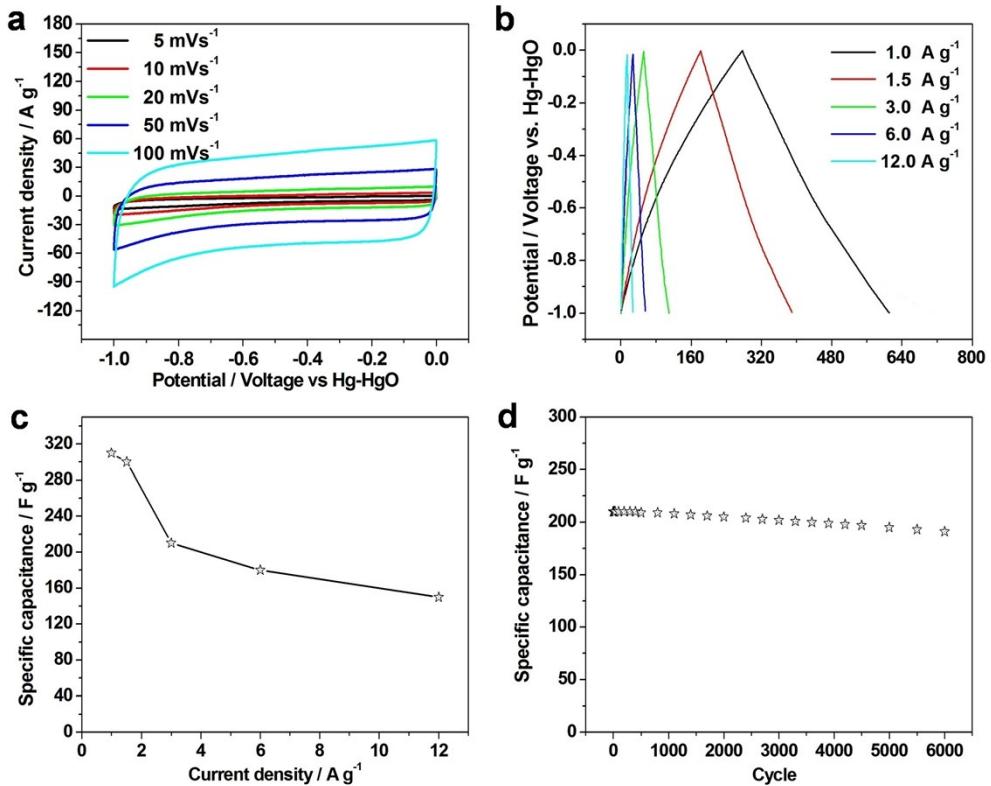


Figure S8. a) Cyclic voltammetry within -1.0 to 0 V range at different scan rates of 5-100 mV s^{-1} was performed on the as-prepared N,S co-doped pure carbon architectures (600 °C) electrodes in 3.0 M KOH at room temperature, b) The galvanostatic discharge curves at 1.0-12.0 A g^{-1} , c) Specific capacitance obtained from different current densities, and d) Cycling performance of the device at 3.0 A g^{-1} for 6000 cycles.

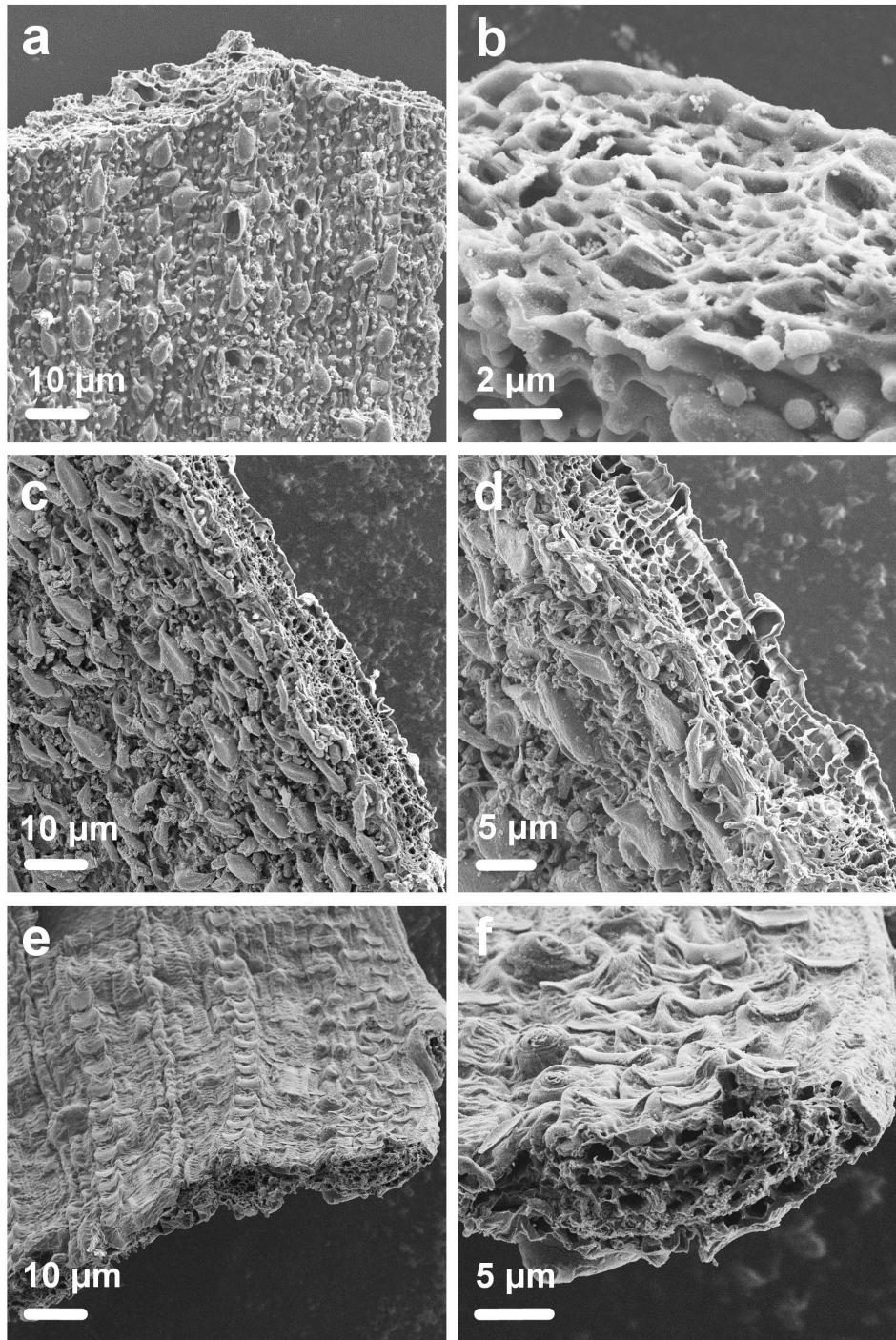


Figure S9 SEM images of N,S co-doped pure carbon architectures obtained with different calcination temperatures: a, b) 600 °C, c, d) 800 °C and e, f) 900 °C.

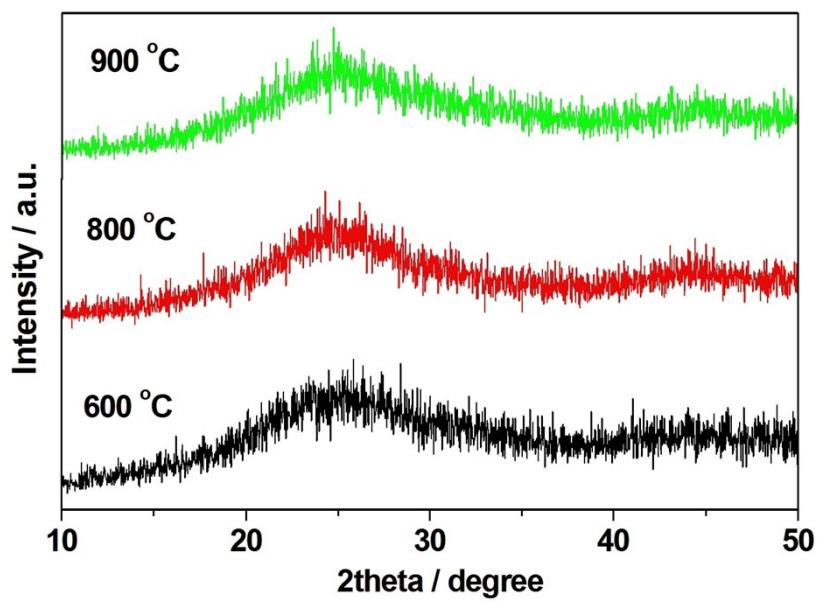


Figure S10 XRD patterns of N,S co-doped pure carbon architectures obtained with different calcination temperatures: 600 °C, 800 °C and 900 °C.

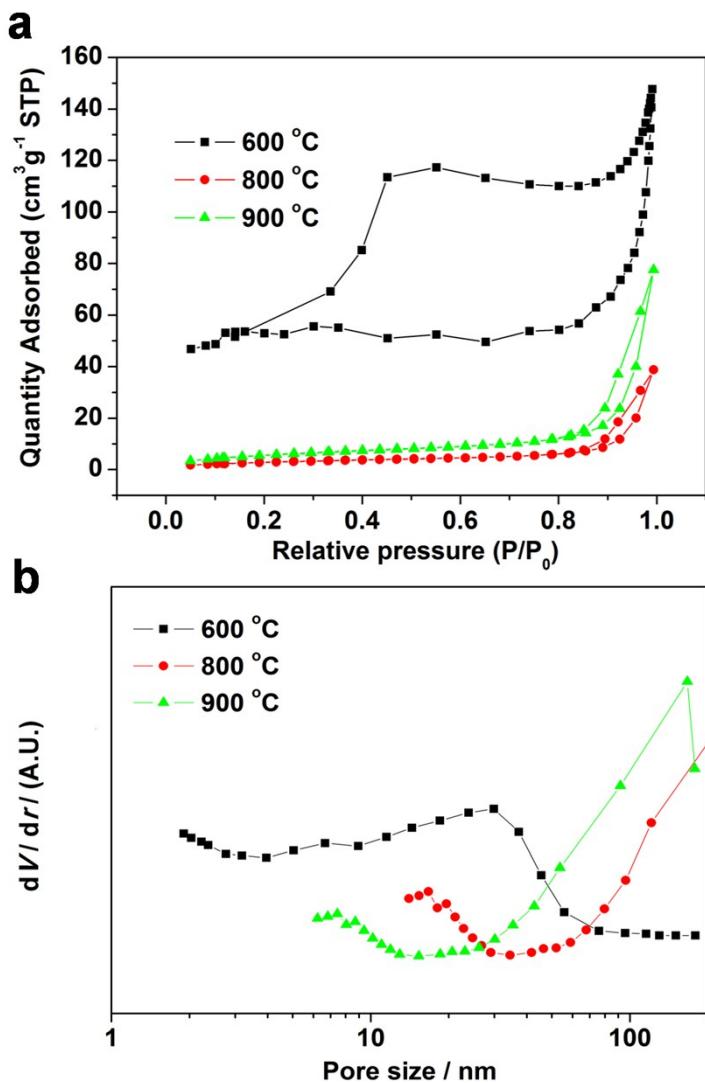


Figure S11. a) The corresponding N₂ adsorption-desorption isotherms, and b) The corresponding pore size distribution curve of N,S co-doped pure carbon architectures obtained with different calcination temperatures: 600 °C, 800 °C and 900 °C.

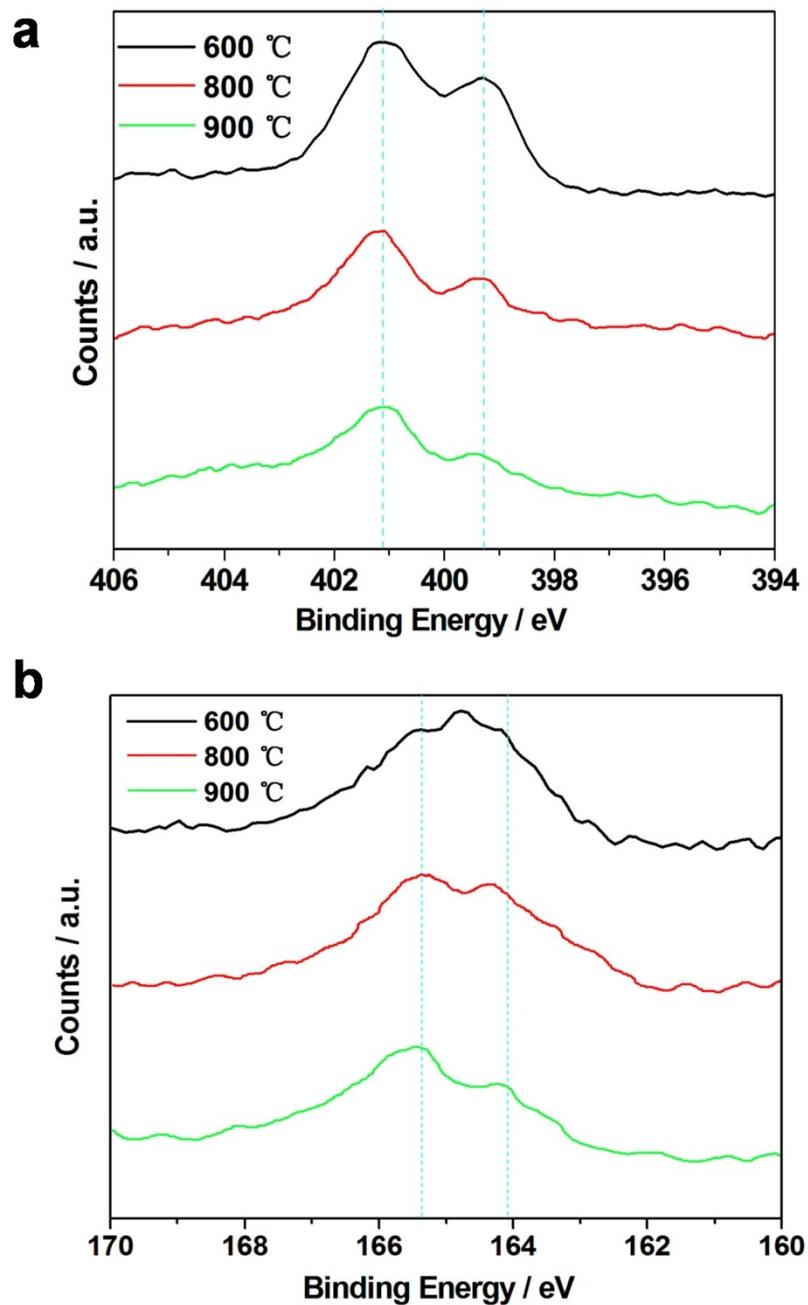


Figure S12. The high-resolution XPS spectra of N,S co-doped pure carbon architectures obtained with different calcination temperatures: 600 °C, 800 °C and 900 °C, a) N 1s, and b) S 2p.

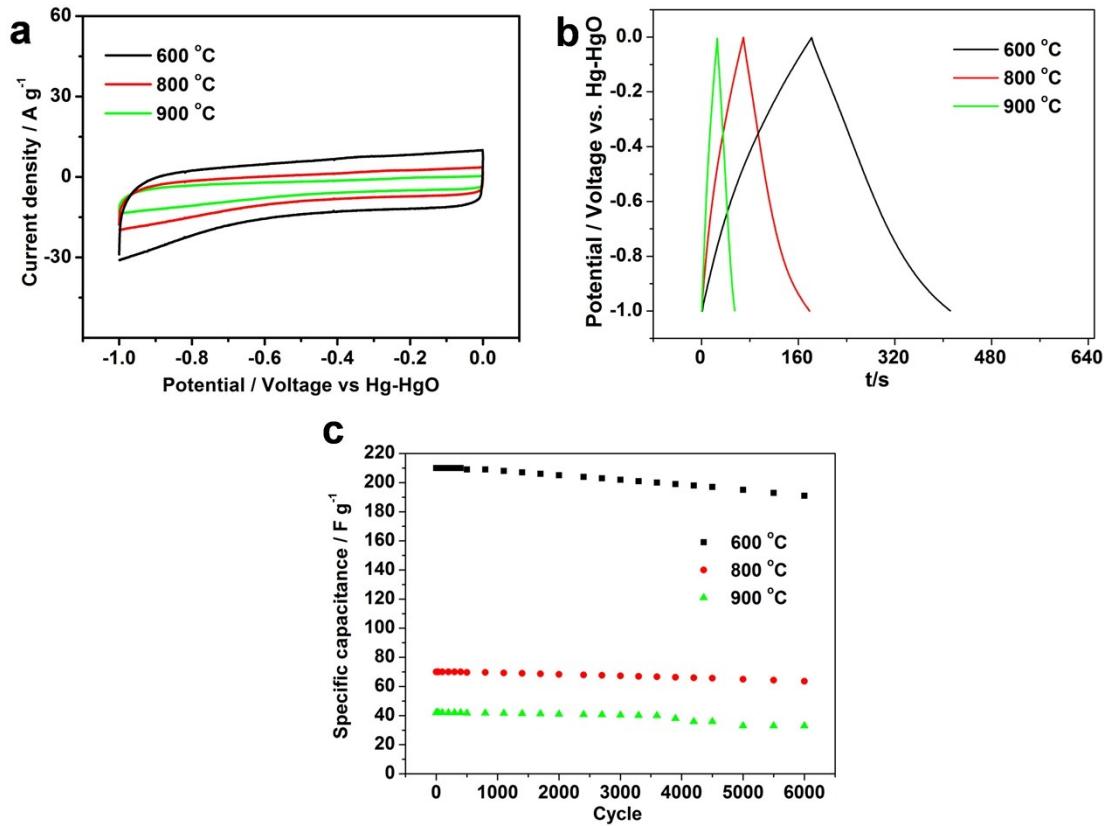


Figure S13. The as-prepared N,S co-doped pure carbon architectures (600 °C, 800 °C and 900 °C) electrodes in 3.0 M KOH at room temperature: a) Cyclic voltammetry within -1.0 to 0 V range at a scan rate of 20 $\text{mV}\cdot\text{s}^{-1}$, b) The galvanostatic discharge curves at 1.5 A g^{-1} , and c) Cycling performance of the device at 3.0 A g^{-1} for 6000 cycles.

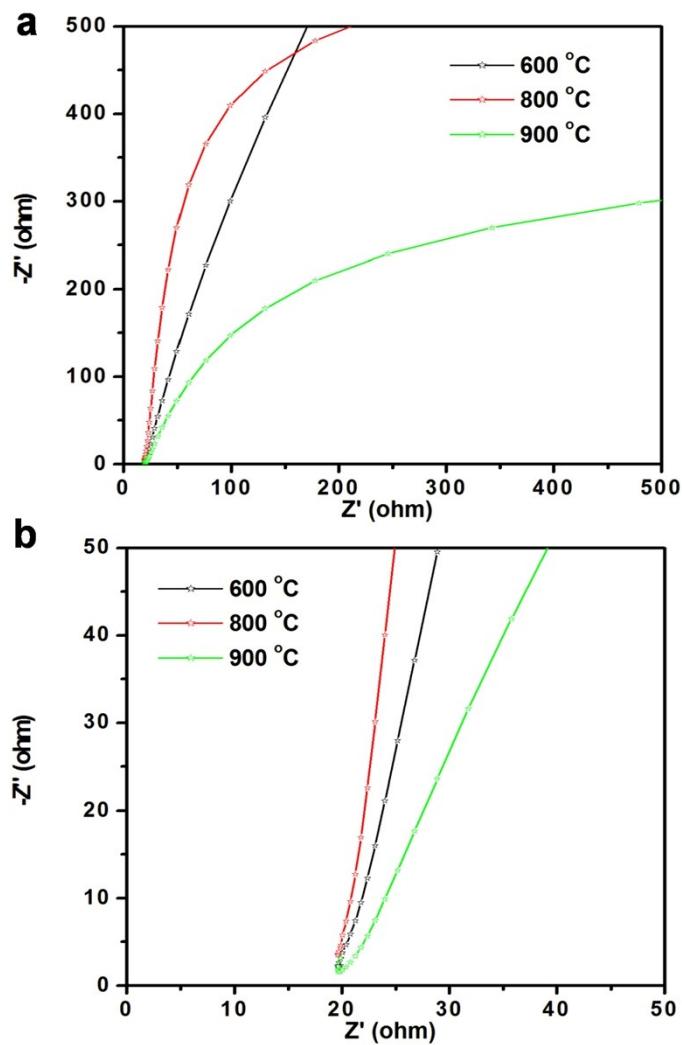


Figure S14. Electrochemical impedance spectra (EIS) image of the the as-prepared N,S co-doped pure carbon architectures (600 °C, 800 °C and 900 °C) electrodes in 3.0 M KOH, a) 0-500 Ohm, and b) 0-50 Ohm.

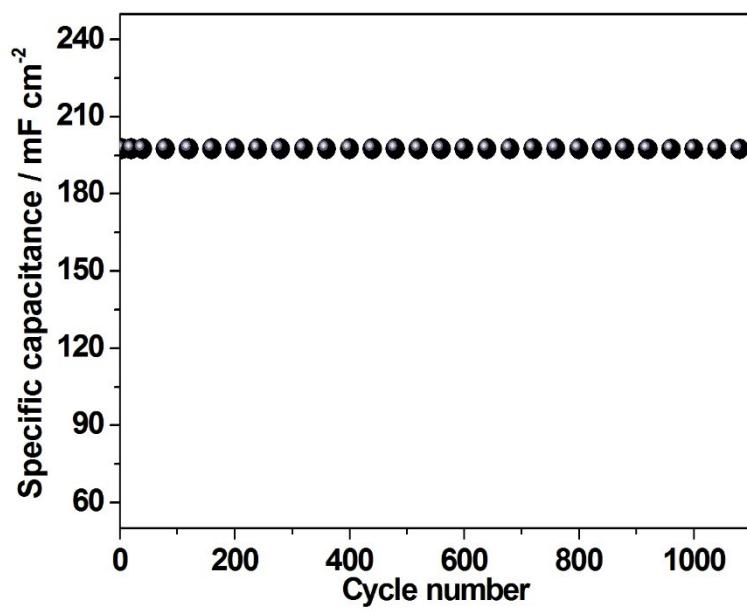


Figure S15. The mechanical stability (1000 cycles of bending 90° at 8.0 Am cm⁻²) of the NS-C-CoSiO//Activated carbon flexible solid-state asymmetric supercapacitors.

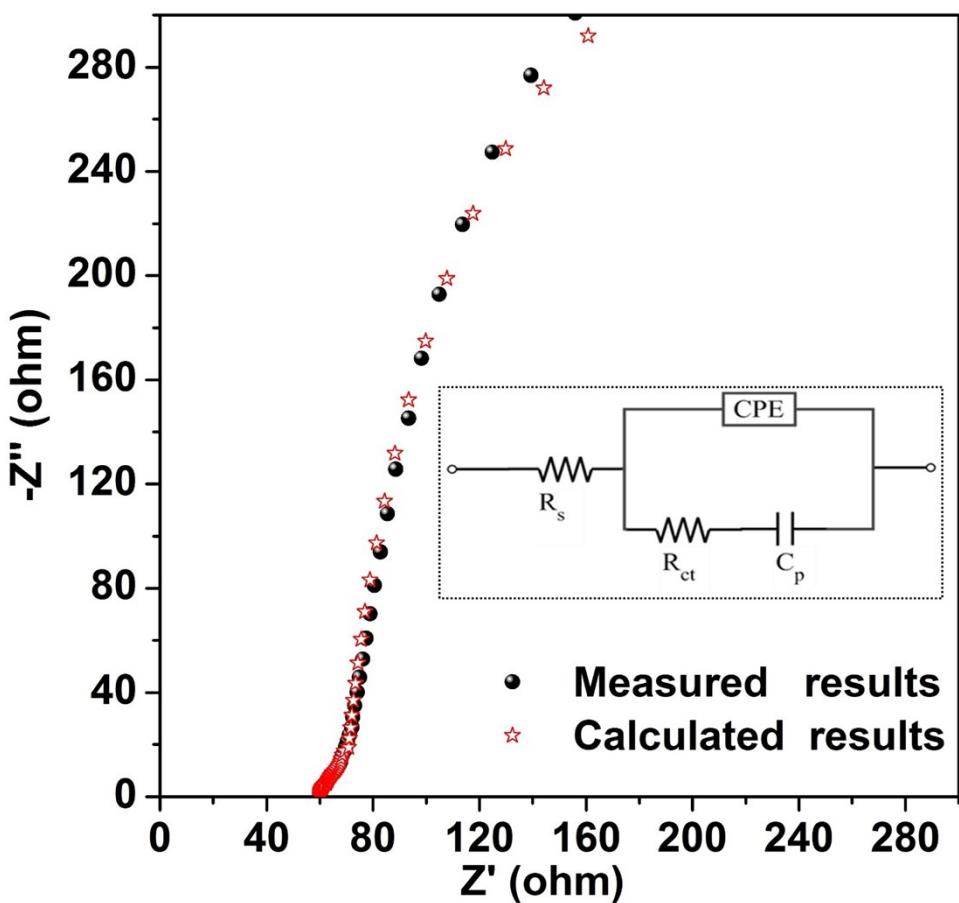


Figure S16. Electrochemical impedance spectra (EIS) image of the NS-C-CoSiO // activated carbons device.

Table S1. The Co/Si weight% is further analyzed and confirmed by inductively coupled plasma-atomic emission spectrometry (ICP-AES), and the atom ratio of Co/Si is 3.01:2.

Element	W/%
Co	22.3
Si	7.1

Table S2. Some previous Co-based nanomaterials for supercapacitor in three-electrode system.^[1-21]

Micro/nanostructures	Capacitance, 1 A g⁻¹ / F g⁻¹	Ref.
β -Co(OH) ₂ single layer	2028	1
Ni _x Co-OH/GO sheets	1540	2
Co ₃ O ₄ thin sheets	1500	3
Ni-Co-S nanoparticles	1492	4
The MnO ₂ -NPs@Co/C	1050	5
NiCo ₂ O ₄ /GO composites	1211.25	6
LiCoO ₂ particles	1050	7
NiCo ₂ S ₄ ball-in-ball hollow spheres	1036	8
Ni _x Co _{3-x} O ₄ nanoparticles	800	9
CoFS sheets	711.3	10
Co ₃ O ₄ nanotubes	647	11
CoCO ₃ /CoO/carbon cloth	510	12
Mesoporous Co ₃ O ₄ nanoflakes	450	13
Co ₃ O ₄ @CNT/polyindole composite	442.5	14
Co ₂ P nanoflake/carbon cloth	430	15
Co ₂ (OH) ₂ CO ₃ /activated carbon	301.44	16
Co _{0.85} Se//N-PCNs	290	17
α -Co(OH) ₂ /carbon nanofoam	210	18
CoMoO ₄ nanospheres	170	19
Layered (Ni,Co) ₃ Si ₂ O ₅ (OH) ₄	150	20
Hollow porous Co ₃ O ₄ nanospheres	150	21
3D mesoporous C-Co₃Si₂O₅(OH)₄	1600	This work

Table S3. The N and S content of as-prepared N,S co-doped pure carbon architectures (600 °C, 800 °C and 900 °C).

	N wt %	S wt %
Sample-600	2.7	1.8
Sample-800	1.5	0.7
Sample-900	0.8	0.4

Table S4. The N/C and S/C atomic ratio of as-prepared N,S co-doped pure carbon architectures (600 °C, 800 °C and 900 °C).

	N/C(%)	S/C(%)
Sample-600	2.4	0.7
Sample-800	1.3	0.3
Sample-900	0.7	0.2

Table S5. The percentages of the graphitic-N, pyridinic-N, and pyrrolic-N of as-prepared N,S co-doped pure carbon architectures (600 °C, 800 °C and 900 °C).

	Pyridinic-N(%)	Pyrrolic-N(%)	Graphitic-N(%)
Sample-600	35.2	33.8	31
Sample-800	33.9	35.6	30.5
Sample-900	31.6	34.8	33.6

References

- [1] S. Gao, Y. F. Sun, F. C. Lei, L. Liang, J. W. Liu, W. T. Bi, B. C. Pan, Y. Xie, *Angew. Chem. Int. Ed.*, 53 (2014) 12789.
- [2] H. Ma, J. He, D. B. Xiong, J. S. Wu, Q. Q. Li, V. Dravid, Y. F. Zhao, *ACS Appl. Mater. Inte.*, 8 (2016) 1992.
- [3] Y. Q. Jiang, L.Y. Chen, H. Q. Zhang, Q. Zhang, W. F. Chen, J. K. Zhu, D. M. Song, *Chem. Eng. J.*, 292 (2016) 1.
- [4] J. Yang, C. Yu, X. M. Fan, S. X. Liang, S. F. Li, H. W. Huang, Z. Ling, C. Hao, J. S. Qiu, *Energy Environ. Sci.*, 9 (2016) 1299.
- [5] J. Zhi, O. Reiser, F. Q. Huang, *ACS Appl. Mater. Inte.*, 8 (2016) 8452.
- [6] Y. J. Xu, L. C. Wang, P. Q. Cao, C. L. Cai, Y. B. Fu, X. H. Ma, *J. Power Sources*, 306 (2016) 742.
- [7] Y. N. Xu, Y. Y. Dong, X. Han, X. F. Wang, Y. J. Wang, L. F. Jiao, H. T. Yuan, *ACS Sustainable Chem. Eng.* 3 (2015) 2435.
- [8] L. F. Shen, L. Yu, H. B. Wu, X. Y. Yu, X. G. Zhang, X. W. (David) Lou, *Nat. Commun.*, (2015) DOI:10.1038/ncomms7694.
- [9] S. R. Chen, M. Xue, Y. Q. Li, Y. Pan, L. K. Zhu, S. L. Qiu, *J. Mater. Chem. A*, 3 (2015) 20145.
- [10]W. Yang, Y. Y. Feng, N. Wang, H. Y. Yuan, D. Xiao, *J. Alloy. Compd.*, 644 (2015) 836.
- [11]H. Li, F. Yue, C. Yang, P. Qiu, P. Xue, Q. Xu, J. D Wang, *Ceram. Int.* 42 (2016) 3121.

- [12] J. Xu, S. Cheng, L. F. Yang, Y. Jiang, Z. J. Jiang, C. H. Yang, H. Zhang, M. L. Liu, *Nano Energy*, 11 (2015) 736.
- [13] A. G. Xiao, S. B. Zhou, C. G. Zuo, Y. B. Zhuan, X. Ding, *Mater. Res. Bull.* 60 (2014) 674.
- [14] X. Zhou, A. Q. Wang, Y. M. Pan, C. F. Yu, Y. Zou, Y. Zhou, Q. Chen, S. S. Wu, *J. Mater. Chem. A*, 3 (2015) 13011.
- [15] X. J. Chen, M. Cheng, D. Chen, R. M. Wang, *ACS Appl. Mater. Inte.* 8 (2016) 3892.
- [16] T. M. Masikhwa, J. K. Dangbegnon, A. Bello, M. J. Madito, D. Momodu, N. Manyala, *J. Phys. Chem. C*, 88 (2016) 60.
- [17] H. Peng, G. F. Ma, K. J. Sun, Z. G. Zhang, J. D. Li, X. Z. Zhou, Z. Q. Lei, *J. Power Sources*, 297 (2015) 351.
- [18] R. D. Noce, S. Eugenio, T. M. Silva, M. J. Carmezim, M. F. Montemor, *J. Power Sources*, 288 (2015) 234.
- [19] M. J. Barmi, M. M. Sundaram, *RSC Adv.* 6 (2016) 36152.
- [20] Q. Rong, L. L. Long, X. Zhang, Y. X. Huang, H. Q. Yu, *Appl. Energ.* 153 (2015) 63.
- [21] F. L. Meng, Z. G. Fang, Z. X. Li, W. W. Xu, M. J. Wang, Y. P. Liu, J. Zhang, W. R. Wang, D. Y. Zhao, X. H. Guo, *J. Mater. Chem. A*, 1 (2013) 7235.